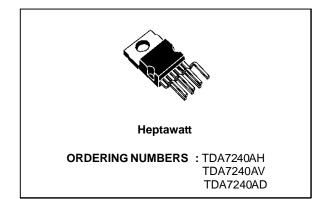


20W BRIDGE AMPLIFIER FOR CAR RADIO

- COMPACT HEPTAWATT PACKAGE
- FEW EXTERNAL COMPONENTS
- OUTPUT PROTECTED AGAINST SHORT CIRCUITS TO GROUND AND ACROSS LOAD
- DUMP TRANSIENT
- THERMAL SHUTDOWN
- LOUDSPEAKER PROTECTION
- HIGH CURRENT CAPABILITY
- LOW DISTORTION/LOW NOISE

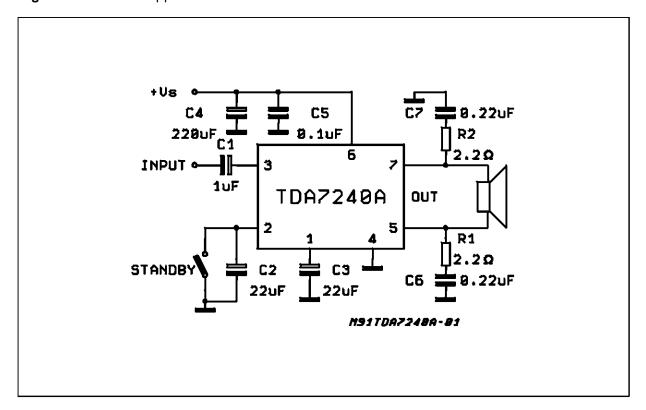


DESCRIPTION

The TDA7240A is a 20W bridge audio amplifier IC designed specially for car radio applications. Thanks to the low external part count and compact Heptawatt 7-pin power package the TDA7240A occupies little space on the printed circuit board.

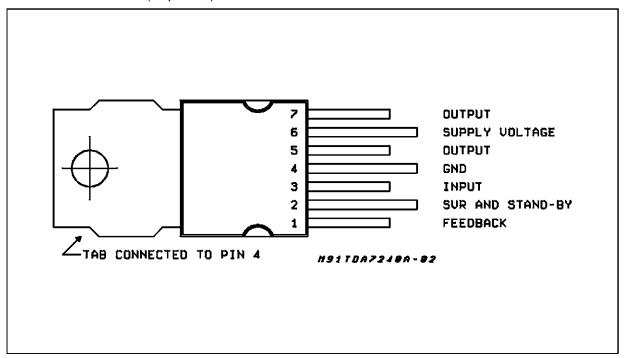
Reliable operation is guaranteed by a comprehensive array of on-chip protection features. These include protection against AC and DC output short circuits (to ground and across the load), load dump transients, and junction overtemperature. Additionally, the TDA7240A protects the loudspeaker when one output is short-circuited to ground.

Figure 1: Test and Application Circuit



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PION CONNECTION (Top view)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Operating Supply Voltage	18	V
Vs	DC Supply Voltage	28	V
Vs	Peak Supply Voltage (for 50ms)	40	V
I _o (*)	Peak Output Current (non repetitive t = 0.1ms)	4.5	Α
I _o (*)	Peak Output Current (repetitive f ≥10Hz)	3.5	Α
P _{tot}	Power Dissipation at Tcase = 85°C	16	W
T _{stg} , T _j	Storage and Junction Temperature	-40 to 150	°C

^(*) Internally limited

THERMAL DATA

	Symbol Parameter		Value	Unit
ſ	R _{th j-case}	Thermal Resistance Junction-case Max.	4	V



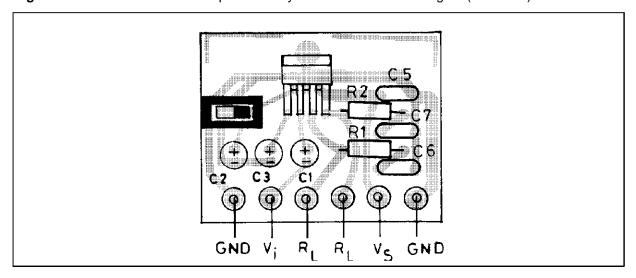
ELECTRICAL CHARACTERISTICS (refer to the circuit of fig. 1, $T_{amb} = 25^{\circ}C$, R_{th} (heatsink) = $4^{\circ}C/W$, $V_s = 14.4V$)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage				18	V
Vos	Output Offset Voltage				150	mV
l _d	Total Quiescent Current	$R_L = 4\Omega$		65	120	mA
Po	Output Power	$f = 1 \text{kHz}; d = 10\%$ $R_L = 49$ $R_L = 89$		20 12		&
d	Distortion	$R_L = 4\Omega$ f = 1kHz P _o = 50mW to 12W		0.1	0.5	%
		$R_L = 8\Omega$ $f = 1kHz$ $P_o = 50mW$ to 12W		0.05	0.5	%
GV	Voltage Gain	f = 1KHz	39.5	40	40.5	dB
SVR	Supply Voltage Rejection	$f = 100Hz$ $R_g = 10K\Omega$	35	40		dB
E _N	Total Input Noise	$R_g = 10 \text{K}\Omega$		2 3	10	μV μV
η	Efficiency	$R_L = 4\Omega$ $f = 1KHz$		65		%
I _{sb}	Stand-by Current			200		μΑ
R _i	Input Resistance	f = 1kHz	70			kΩ
Vi	Input Sensitivity	$f = 1kHz; P_0 = 2W; R_L = 4\Omega$		28		mV
f∟	Low Frequency Roll Off (-3dB)	Po = 15W; $R_L = 4\Omega$			30	Hz
f _H	High Frequency Roll Off (–3dB)	Po = 15W; $RL = 4\Omega$	25			kHz
As	Stand-by Attenuation	V _o = 2Vrms	70	90		dB
V _{TH (pin2)}	Stand-by Threshold				1	V

(*) B= Curve A

(**) B = 22Hz to 22 KHz

Figure 2: P.C. Board and Components layout of the Circuit of Fig. 1.(1:1scale)



APPLICATION SUGGESTION

The recommended values of the components are those shown on application circuit of Fig. 1. Different values can be used, the following table can help the designer.

Component	Recommended Value	Purpose	Larger Than	Smaller Than
R1, R2	2.2Ω	Frequency Stability	Danger of High Frequency Oscillation	
C1	1μF	Input DC Decoupling	Higher Turn On and Stand-by Delay	Higher Turn On Pop. Higher Low Frequency Cutoff
C2	22μF	Ripple Rejection	Increase of SVR Increase of the Turn On Delay	Degradation of SVR
C3	22μF	Feedback low Frequency Cutoff		Higher Low Frequency Cutoff
C6, C7	0.22μF	Frequency Stability		Danger of Oscillation
C4	220μF	Supply Filter		Danger of Oscillation
C5	0.1μF	Supply Bypass		Danger of Oscillation

Figure 3: Output Power vs. Supply Voltage.

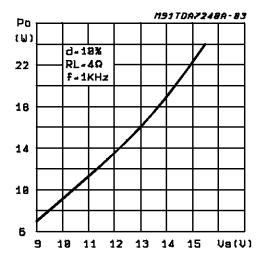


Figure 5: Output Power vs. Supply voltage.

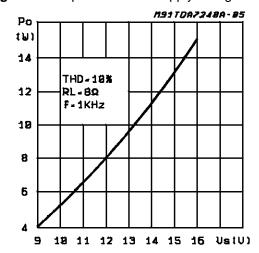


Figure 4: Distortion vs. Output Power.

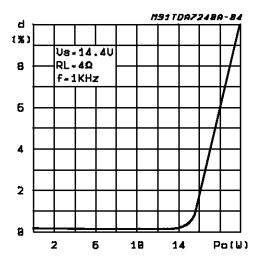


Figure 6: Distortion vs. Output Power.

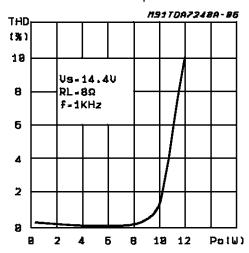


Figure 7: Distortion vs. Frequency.

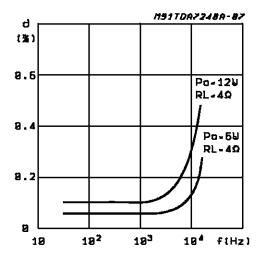


Figure 9 : Power Dissipation and Efficiency vs. Output Power.

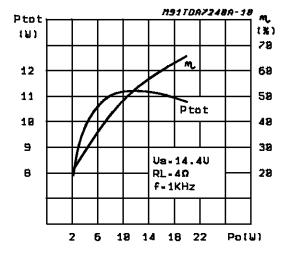


Figure 8 : Supply Voltage Rejection vs. Frequency.

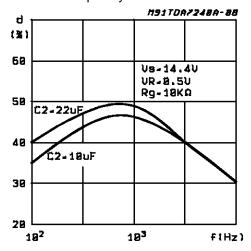
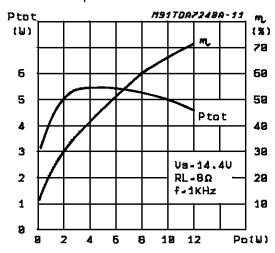
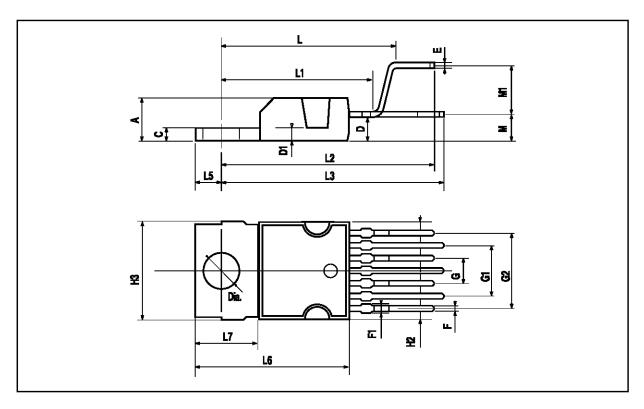


Figure 10 : Power Dissipation and Efficiency vs. Output Power.



HEPTAWATT PACKAGE MECHANICAL DATA

DIM.	mm			inch			
الااالط. ــــــــــــــــــــــــــــــــــــ	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			4.8			0.189	
С			1.37			0.054	
D	2.4		2.8	0.094		0.110	
D1	1.2		1.35	0.047		0.053	
Е	0.35		0.55	0.014		0.022	
F	0.6		0.8	0.024		0.031	
F1			0.9			0.035	
G	2.41	2.54	2.67	0.095	0.100	0.105	
G1	4.91	5.08	5.21	0.193	0.200	0.205	
G2	7.49	7.62	7.8	0.295	0.300	0.307	
H2			10.4			0.409	
H3	10.05		10.4	0.396		0.409	
L		16.97			0.668		
L1		14.92			0.587		
L2		21.54			0.848		
L3		22.62			0.891		
L5	2.6		3	0.102		0.118	
L6	15.1		15.8	0.594		0.622	
L7	6		6.6	0.236		0.260	
М		2.8			0.110		
M1		5.08			0.200		
Dia	3.65		3.85	0.144		0.152	



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